Notice of Allowability	Application No.	Applicant(s)	
	10/706,902	CHAE ET AL.	
	Examiner	Art Unit	
	Binh X. Tran	1765	
	Dilit A. Hall	1700	I
The MAILING DATE of this communication apperature All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this app or other appropriate communication GHTS. This application is subject to	plication. If not include will be mailed in due	ed course. THIS
1. \boxtimes This communication is responsive to <u>10-17-2006</u> .		•	
2. The allowed claim(s) is/are 1 and 3-42.			
3. ☐ Acknowledgment is made of a claim for foreign priority una) ☐ All b) ☐ Some* c) ☐ None of the: 1. ☐ Certified copies of the priority documents have	been received.		
2. Certified copies of the priority documents have	• • • • • • • • • • • • • • • • • • • •		tion from the
3. Copies of the certified copies of the priority doc	cuments have been received in this r	national stage applica	tion from the
International Bureau (PCT Rule 17.2(a)). * Certified copies not received:			
•			
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the red	quirements
4. A SUBSTITUTE OATH OR DECLARATION must be subminiformal PATENT APPLICATION (PTO-152) which give			OTICE OF
5. CORRECTED DRAWINGS (as "replacement sheets") mus	t be submitted.		
(a) I including changes required by the Notice of Draftspers	on's Patent Drawing Review (PTO-9	948) attached	
1) 🗌 hereto or 2) 🔲 to Paper No./Mail Date			
(b) ☐ including changes required by the attached Examiner's Paper No./Mail Date	s Amendment / Comment or in the O	ffice action of	
Identifying indicia such as the application number (see 37 CFR 1, each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on the drawin ne header according to 37 CFR 1.121(c	gs in the front (not the i).	back) of
6. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT I	sit of BIOLOGICAL MATERIAL m FOR THE DEPOSIT OF BIOLOGICA	nust be submitted. N AL MATERIAL.	Note the
Attachment(s)			
1. X Notice of References Cited (PTO-892)	5. Notice of Informal Page	atent Application	
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. Interview Summary	(PTO-413),	
Information Disclosure Statements (PTO/SB/08), Paper No./Mail Date	Paper No./Mail Date ements (PTO/SB/08), 7. Examiner's Amendment/Comment		
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. Examiner's Statement of Reasons for Allowance		
	9.	9.	
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DETAILED ACTION

Response to Amendment

1. The applicant's amendment is sufficient to overcome the examiner's previous 35 USC 112, 2nd paragraph rejection.

Allowable Subject Matter

- 2. Claims 1, 3-42 are allowed.
- The following is an examiner's statement of reasons for allowance: Respect to 3. claims 1, 3-18, the cited prior arts fail to discloses the step of selectively etching the sacrificial light absorbing material over a dielectric layer using a gas mixture comprises a hydrofluorocarbon gas, a nitrogen-containing gas, an oxygen-containing gas, an inert gas and at least one of a hydrogen-containing gas or a fluorine-rich fluorocarbon gas in combination with all other limitations in the claims. Respect to claims 19-38, 41-42, the cited prior arts fail to disclose the step of removing the photoresist layer and sacrificial light absorbing material using a gas mixture comprising a hydrofluorocarbon gas, a nitrogen-containing gas, an oxygen-containing gas and an inert gas in combination with all other limitations in the claims. Respect to claim 39, the cited prior arts fail to disclose or suggest the step of dissociating an ionized the process gas comprises CH₃F, nitrogen, oxygen, argon and at least one of H₂ or CF₄ to etch sacrificial light absorbing material. The closest prior art (Lee et al. US 2004/0132291) teaches to selectively etch a-dielectric material to form a trench using a mixture of a main gas (e.g. C_xF_y, C_xH_yF_z), an inert gas, and optionally at least one of O₂, N₂ and CO_x (paragraph 0044). Lee

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further teaches to remove the photoresist layer and the remainder of the via filler (160) (i.e. light absorbing material) using H-based plasma obtained from N_2 , N_2/H_2 , NH_3/H_2 , He/H_2 or a mixture thereof.

4. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Binh X. Tran whose telephone number is (571) 272-1469. The examiner can normally be reached on Monday-Thursday and every other Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a

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